

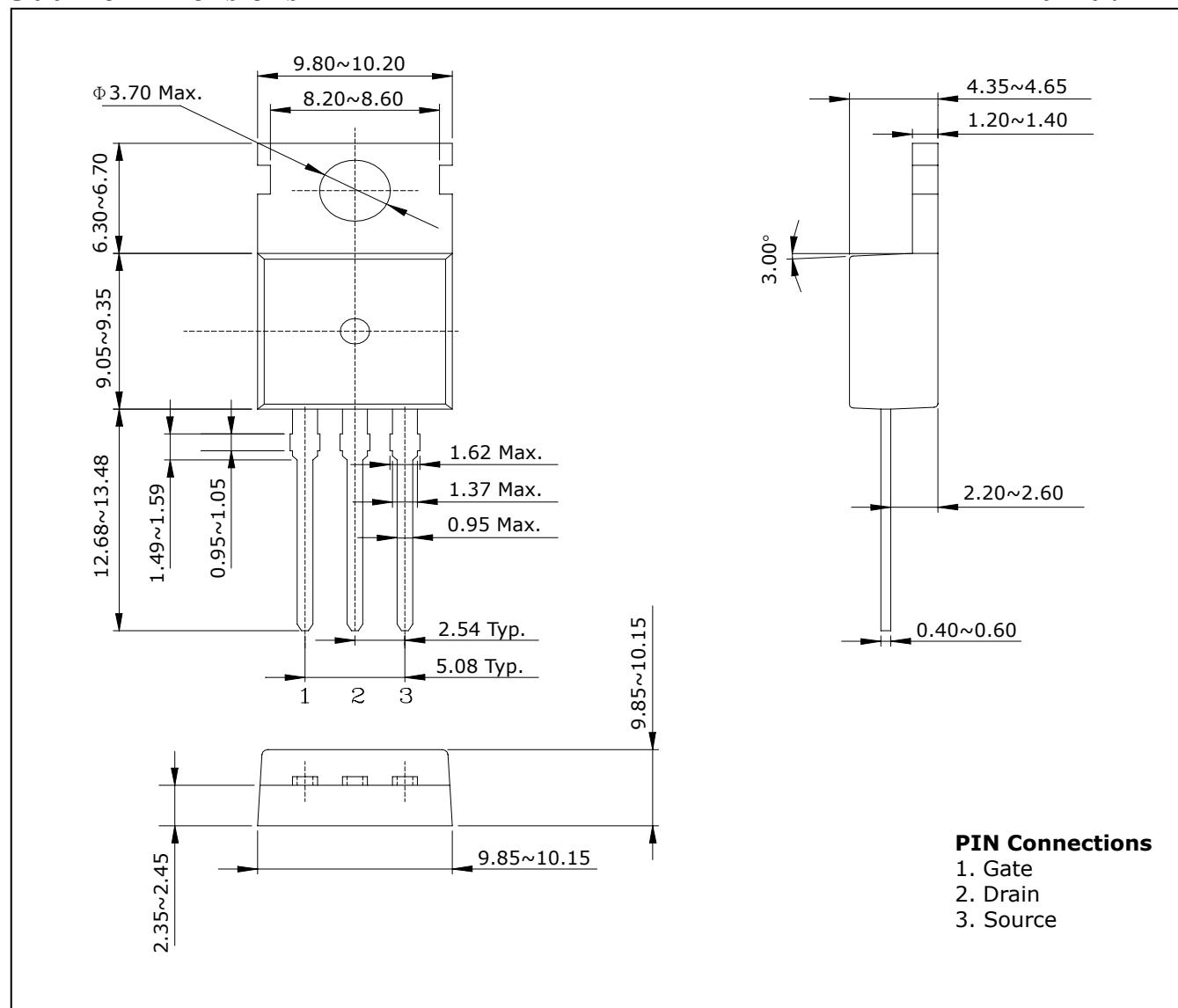
## SWITCHING REGULATOR APPLICATIONS

**Features**

- High Voltage:  $BV_{DSS}=400V$ (Min.)
- Low  $C_{rss}$  :  $C_{rss}=12pF$ (Typ.)
- Low gate charge :  $Qg=28nc$ (Typ.)
- Low  $R_{DS(on)}$  :  $R_{DS(on)}=0.53\Omega$ (Max.)

**Ordering Information**

Type NO.	Marking	Package Code
STK1040P	STK1040	TO-220AB-3L

**Outline Dimensions**


**Absolute maximum ratings**(T<sub>c</sub>=25°C)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	V <sub>DSS</sub>	400	V
Gate-source voltage	V <sub>GSS</sub>	±30	V
Drain current (DC)	I <sub>D</sub>	(T <sub>c</sub> =25°C)	10
		(T <sub>c</sub> =100°C)	4.7
Drain current (Pulsed) *	I <sub>DM</sub>	40	A
Drain power dissipation	P <sub>D</sub>	65	W
Avalanche current (Single) ②	I <sub>AS</sub>	10	A
Single pulsed avalanche energy ②	E <sub>AS</sub>	360	mJ
Avalanche current (Repetitive) ①	I <sub>AR</sub>	10	A
Repetitive avalanche energy ①	E <sub>AR</sub>	8.5	mJ
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	

\* Limited by maximum junction temperature

Characteristic	Symbol	Typ.	Max	Unit
Thermal resistance	R <sub>th(J-C)</sub>	-	1.92	°C/W
	R <sub>th(J-a)</sub>	-	83.3	

## Electrical Characteristics

(Tc=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0	400	-	-	V
Gate threshold voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =250μA, V <sub>DS</sub> = V <sub>GS</sub>	2.0	-	4.0	V
Drain-source cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> =400V, V <sub>GS</sub> =0V	-	-	1	μA
Gate leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V	-	-	±100	nA
Drain-source on-resistance ④	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =5.0A	-	0.46	0.53	Ω
Forward transfer conductance ④	g <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =5.0A	-	6.2	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V f=1MHz	-	950	1430	pF
Output capacitance	C <sub>oss</sub>		-	120	180	
Reverse transfer capacitance	C <sub>rss</sub>		-	12	18	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =200V, I <sub>D</sub> =10A R <sub>G</sub> =25Ω	-	14	-	ns
Rise time	t <sub>r</sub>		-	89	-	
Turn-off delay time	t <sub>d(off)</sub>		-	81	-	
Fall time	t <sub>f</sub>		-	81	-	
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> =200V, V <sub>GS</sub> =10V I <sub>D</sub> =10A	-	28	42	nC
Gate-source charge	Q <sub>gs</sub>		-	4	6	
Gate-drain charge	Q <sub>gd</sub>		-	15	23	

## Source-Drain Diode Ratings and Characteristics

(Tc=25°C)

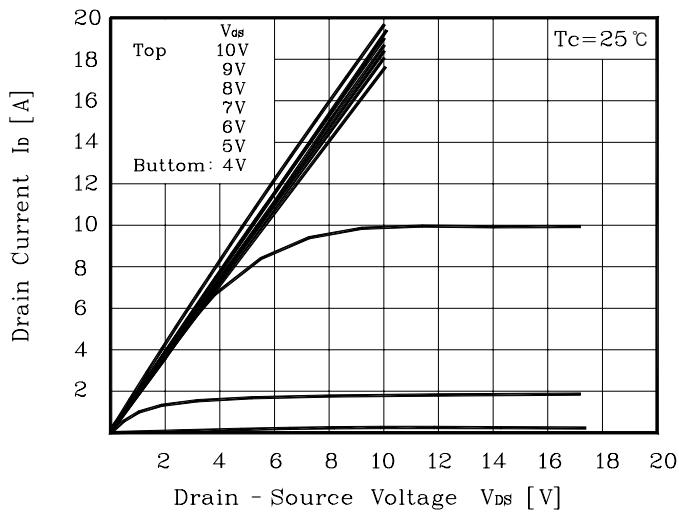
Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Source current (DC)	I <sub>S</sub>	Integral reverse diode in the MOSFET	-	-	10	A
Source current (Pulsed) ①	I <sub>SM</sub>		-	-	40	
Forward voltage ④	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =10A	-	-	1.4	V
Reverse recovery time	t <sub>rr</sub>	I <sub>s</sub> =10A, V <sub>GS</sub> =0, dI <sub>s</sub> /dt=100A/ us	-	290	-	ns
Reverse recovery charge	Q <sub>rr</sub>		-	5.04	-	uC

Note :

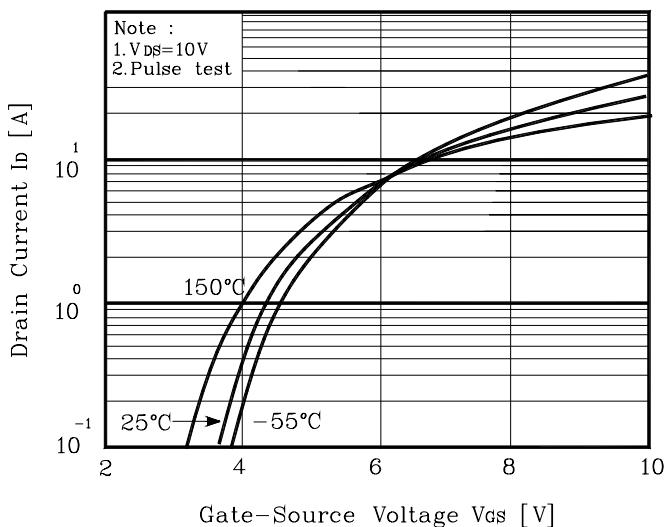
- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② L=6.6mH, I<sub>AS</sub>=10A, V<sub>DD</sub>=50V, R<sub>G</sub>=27Ω
- ③ Pulse Test : Pulse Width < 300us, Duty cycle≤ 2%
- ④ Essentially independent of operating temperature

## Electrical Characteristic Curves

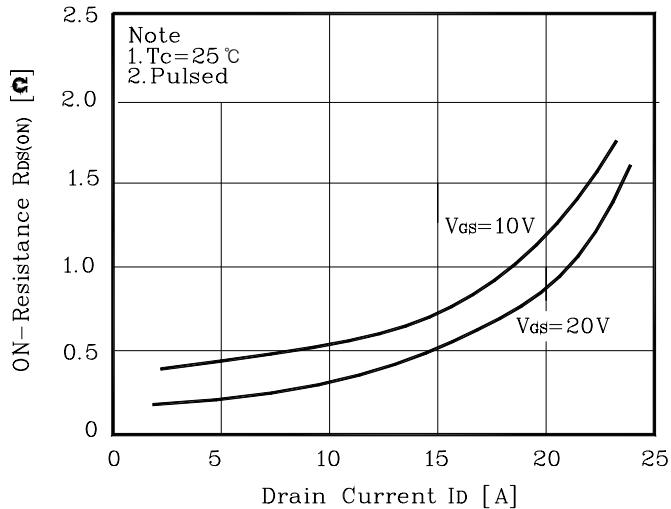
**Fig. 1  $I_D$  -  $V_{DS}$**



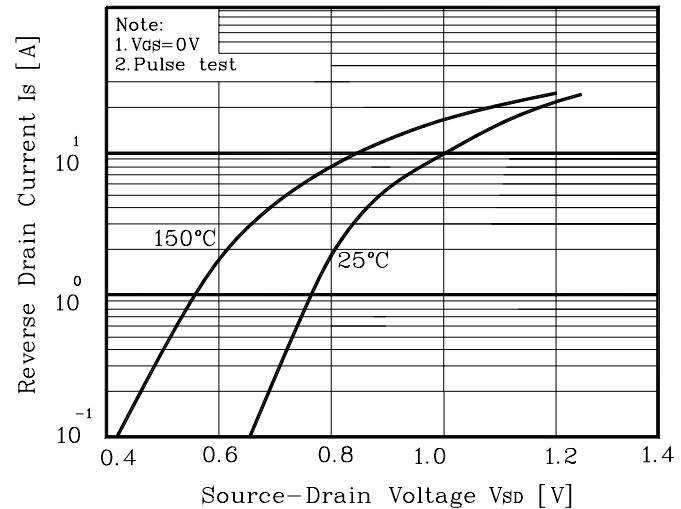
**Fig. 2  $I_D$  -  $V_{GS}$**



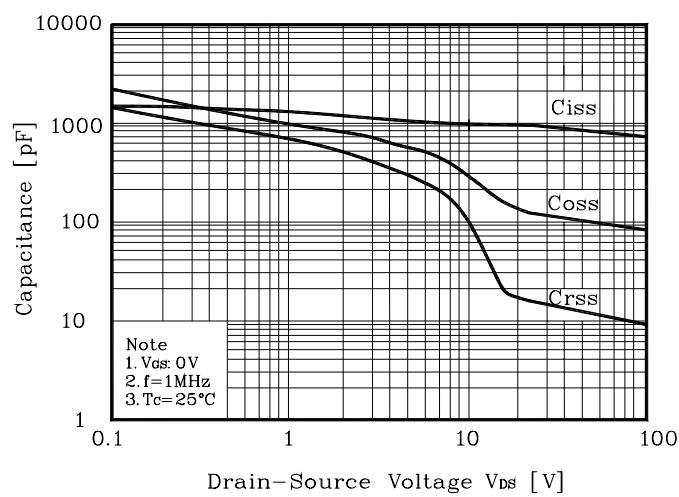
**Fig. 3  $R_{DS(on)}$  -  $I_D$**



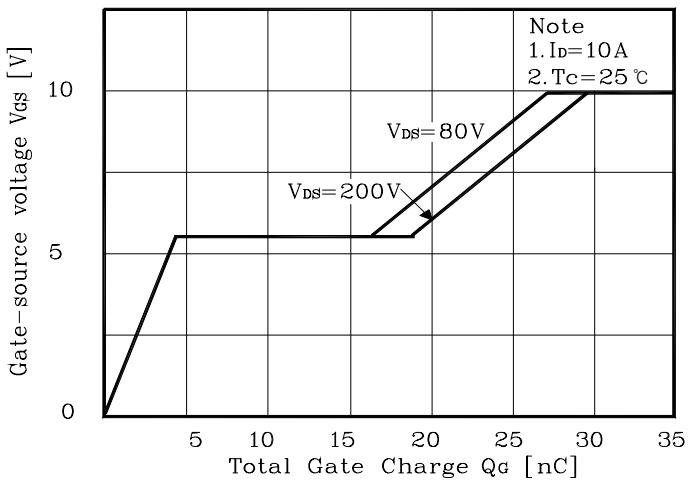
**Fig. 4  $I_S$  -  $V_{SD}$**



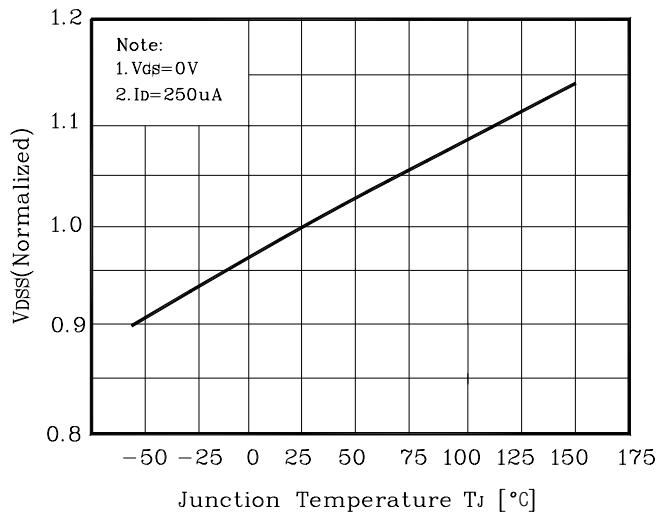
**Fig. 5 Capacitance -  $V_{DS}$**



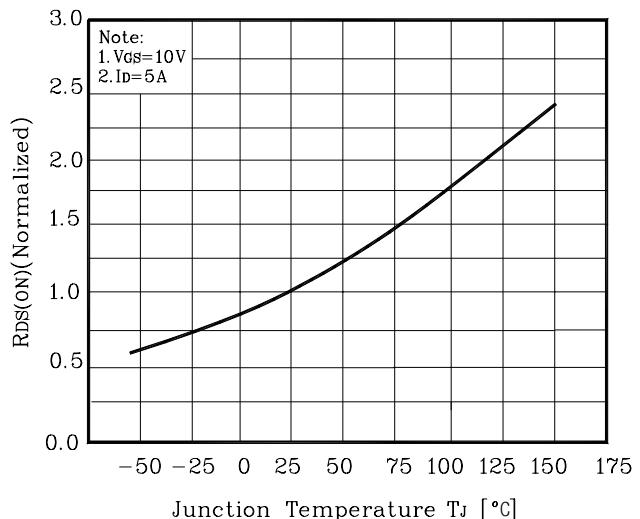
**Fig. 6  $V_{GS}$  -  $Q_G$**



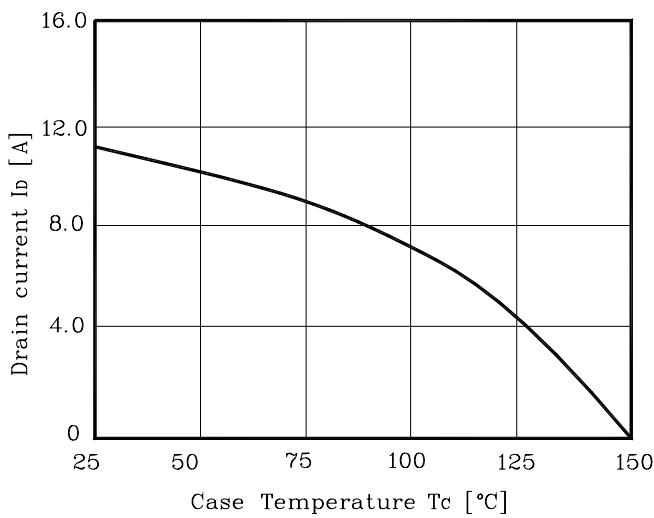
**Fig. 7  $V_{DSS}$  -  $T_J$**



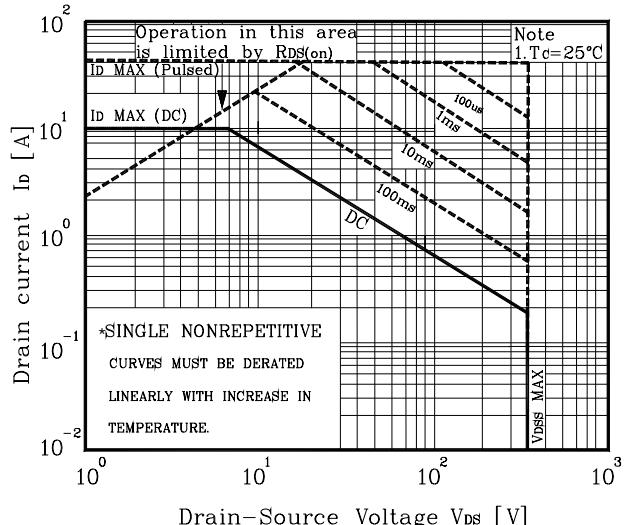
**Fig. 8  $R_{DS(on)}$  -  $T_J$**



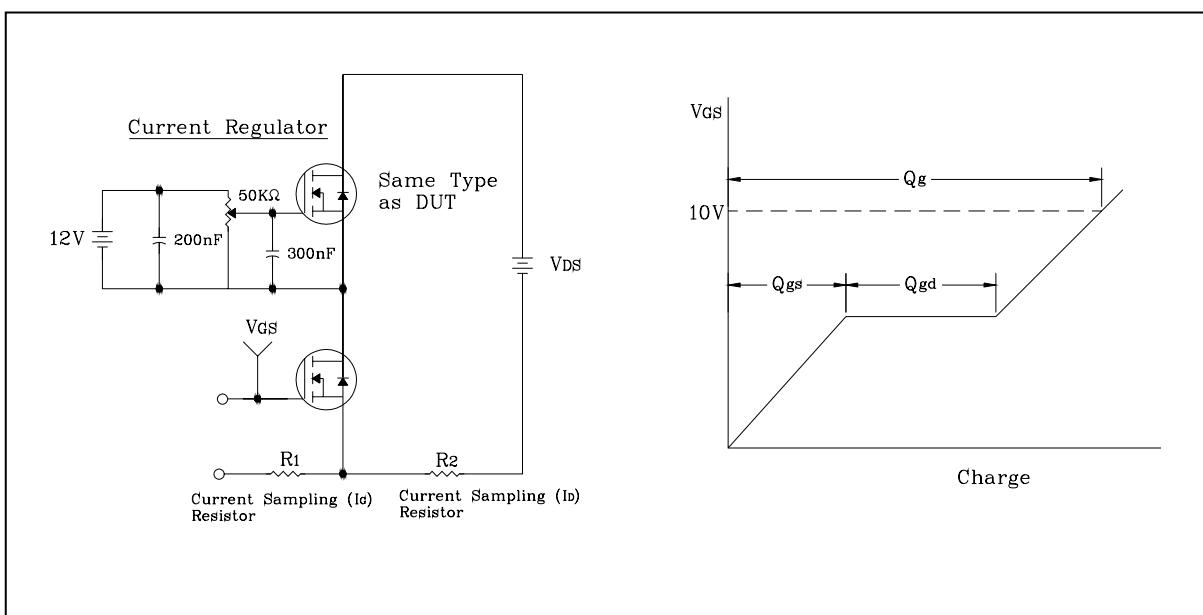
**Fig. 9  $I_D$  -  $T_C$**



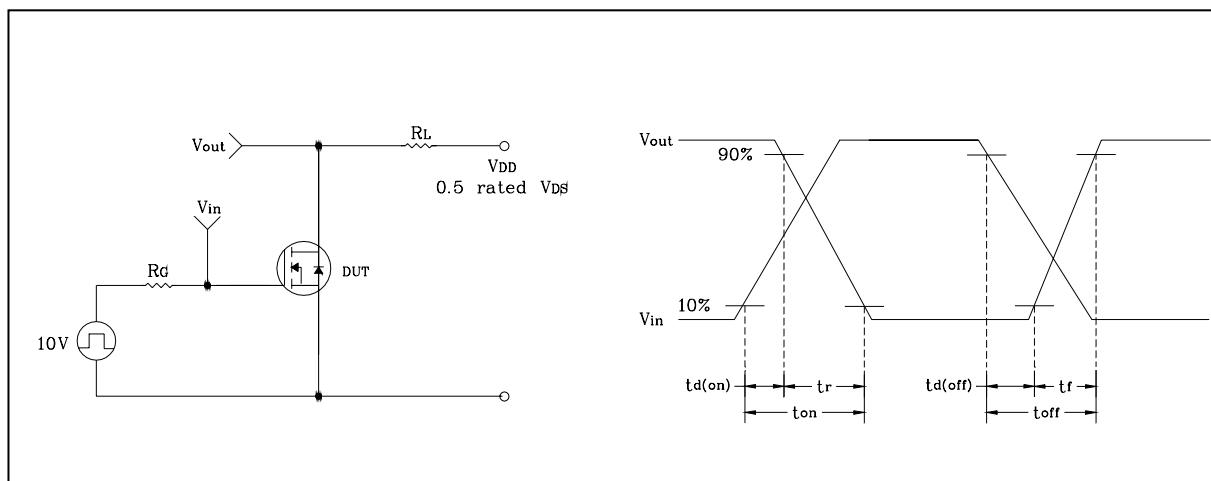
**Fig. 10 Safe Operating Area**



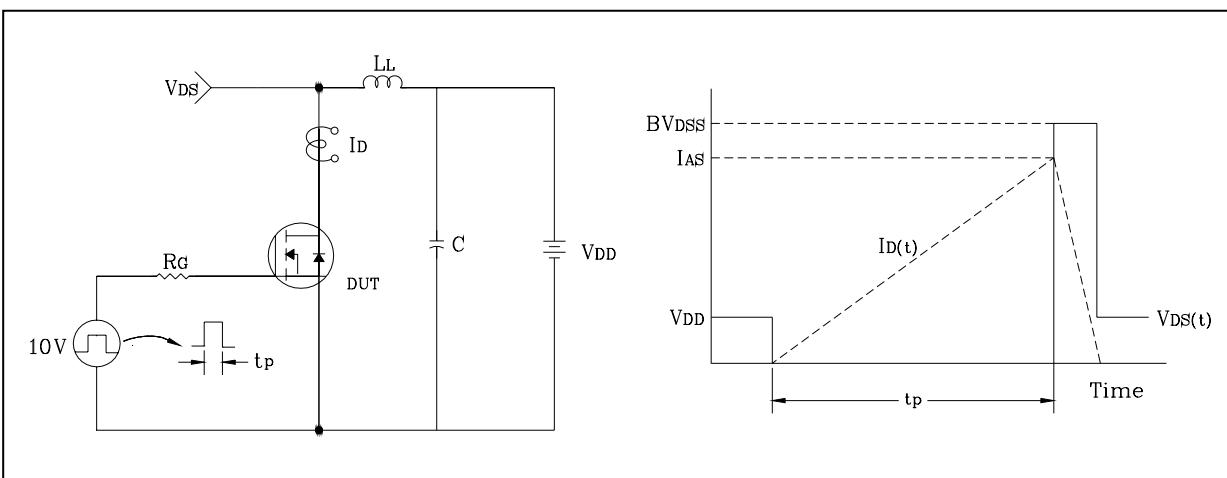
**Fig. 11 Gate Charge Test Circuit & Waveform**



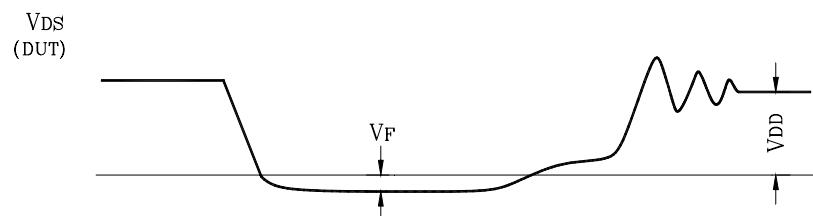
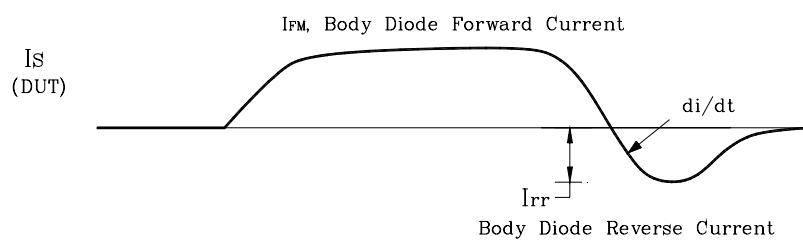
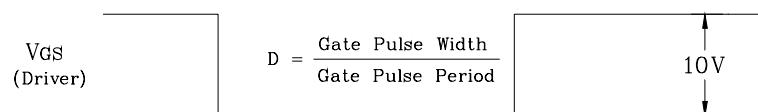
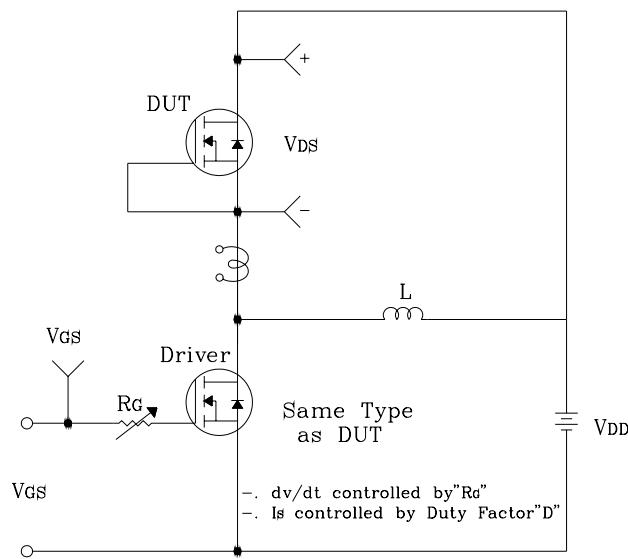
**Fig. 12 Resistive Switching Test Circuit & Waveform**



**Fig. 13 E<sub>AS</sub> Test Circuit & Waveform**



**Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform**



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